

Title (en)
OXYNITRIDE SPUTTERING TARGET

Title (de)
OXYNITRID-SPUTTERING-TARGET

Title (fr)
CIBLE DE PULVERISATION CATHODIQUE D'OXYNITRURE

Publication
EP 2134883 A1 20091223 (FR)

Application
EP 08788046 A 20080326

Priority
• FR 2008050520 W 20080326
• FR 0754340 A 20070406

Abstract (en)
[origin: WO2008132409A1] Sputtering target comprising: - between 30 and 40 at% of a metal, - between 2 and 10 at% nitrogen - between 35 and 50 at% oxygen, - the complement to 100% being composed of at least one element chosen from the group comprising phosphorous (P), boron (B), silicon (Si), germanium (Ge), gallium (Ga), sulphur (S) and aluminium (Al). A method of manufacturing a thin film from the target and an electrochemical device comprising the thin film.

IPC 8 full level
C23C 14/06 (2006.01); **C23C 14/35** (2006.01); **H01M 4/40** (2006.01); **H01M 10/0562** (2010.01); **H01M 10/058** (2010.01); **H01M 10/36** (2010.01); **H01M 10/38** (2006.01); **H01M 50/403** (2021.01); **H01M 50/434** (2021.01)

CPC (source: EP KR US)
C23C 14/0036 (2013.01 - EP US); **C23C 14/06** (2013.01 - KR); **C23C 14/0641** (2013.01 - US); **C23C 14/0676** (2013.01 - EP US); **C23C 14/08** (2013.01 - US); **C23C 14/3407** (2013.01 - KR); **C23C 14/3414** (2013.01 - EP KR US); **H01J 37/3414** (2013.01 - US); **H01J 37/3426** (2013.01 - US); **H01M 6/18** (2013.01 - EP US); **H01M 6/40** (2013.01 - EP US); **H01M 10/0562** (2013.01 - EP US); **H01M 10/058** (2013.01 - EP US); **H01M 50/403** (2021.01 - EP KR US); **H01M 50/434** (2021.01 - EP KR US); **H01J 37/3411** (2013.01 - US); **H01M 2300/0068** (2013.01 - EP US); **H01M 2300/0071** (2013.01 - US); **Y02E 60/10** (2013.01 - EP US); **Y02P 70/50** (2015.11 - EP)

Citation (search report)
See references of WO 2008132409A1

Designated contracting state (EPC)
AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MT NL NO PL PT RO SE SI SK TR

DOCDB simple family (publication)
FR 2914653 A1 20081010; **FR 2914653 B1 20090522**; CN 101652496 A 20100217; CN 101652496 B 20121003; EP 2134883 A1 20091223; JP 2010523815 A 20100715; JP 5599703 B2 20141001; KR 20090127906 A 20091214; KR 20150023850 A 20150305; KR 20160087396 A 20160721; US 2010129722 A1 20100527; US 8728287 B2 20140520; WO 2008132409 A1 20081106

DOCDB simple family (application)
FR 0754340 A 20070406; CN 200880011350 A 20080326; EP 08788046 A 20080326; FR 2008050520 W 20080326; JP 2010501562 A 20080326; KR 20097020672 A 20080326; KR 20157001648 A 20080326; KR 20167018453 A 20080326; US 59399308 A 20080326